WHAT IS CLAIMED IS:

1. A polishing material comprising abrasive grains and a compound represented by a Formula (1).

$R\text{-}O\text{-}(AO)_n\text{-}H$ Formula (1)

In the Formula (1), R is an organic group including a conjugated system, an aryl group, and may include a heteroatom in a carbon skeleton, and $C1/(C1 + C2) \geq 0.4$ holds, where C1 is the number of atoms constituting the conjugated system and C2 is the number of atoms not constituting the conjugated system among atoms constituting the carbon skeleton,

AO represents an oxyalkylene group, and a plurality of the AOs may be the same as or different from each other, and

n is an integer of 2 to 200,

wherein pH of the polishing material is 2.0 to 5.5.

2. The polishing material according to Claim 1, wherein

in an R-O bond of the Formula (1), an R-side atom is a carbon atom constituting the aryl group.

3. The polishing material according to any one of Claims 1 to 2, wherein the R is a hydrocarbon group.

4. The polishing material according to any one of Claims 1 to 3, wherein a compound expressed by the Formula (1) includes an HLB value of 12 to 20.

5. The polishing material according to any one of Claims 1 to 4, wherein the abrasive grains are metal oxide particles.

6. The polishing material according to any one of Claims 1 to 5 further comprising a polymer,

wherein the polymer comprises an anionic polymer,

wherein the anionic polymer includes an aryl group.

7. The polishing material according to any one of Claims 1 to 6 used to expose a patterned surface including a silicon surface on a surface.

8. A polishing method for bringing a surface to be polished into contact with a polishing pad while supplying a polishing material and performing polishing by a relative motion of the surface to be polished and the polishing pad, the polishing method comprising:

polishing the surface to be polished of a semiconductor substrate made of silicon oxide using the polishing material according to any one of Claims 1 to 7 as the polishing material.

9. The polishing method according to Claim 8, wherein

a patterned surface including a silicon surface is exposed on a surface of the semiconductor substrate.